ABSTRACT

STRESSED SEMICONDUCTOR-ON-INSULATOR STRUCTURE RESISTANT TO HIGH-TEMPERATURE STRESS

APPLICANT: S.O.I. TEC (SILICON ON INSULATOR TECHNOLOGIES)

The invention concerns a semiconductor-on-insulator structure, comprising a semiconductor material part and a part made of electrically insulating material, integral with one another, with elastic constraints being present in the semiconductor material part.

The part made of electrically insulating material has a viscosity temperature T_G greater than the viscosity temperature T_{Gsio2} of the SiO_2.

The invention also relates to a process for producing this semiconductor-on-insulator structure.

Figure 1d